NPN SILICON TRANSISTOR 2SC3733

DESCRIPTION

The 2SC3733 is designed for power amplifier and high

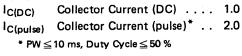
speed switching applications.

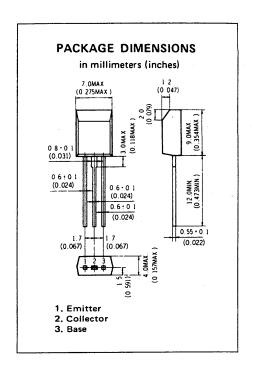
FEATURES

- High speed, high voltage switching.
- Low Collector Saturation Voltage.
- Complementary to the NEC 2SA1460 PNP transistor.

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures Storage Temperature -55 to +150 °C Junction Temperature 150 °C Maximum Maximum Power Dissipation (T_a = 25 °C) Total Power Dissipation Maximum Voltages and Currents (Ta = 25 °C) Collector to Base Voltage . . . V_{CBO} Collector to Emitter Voltage . 45 VCEO Emitter to Base Voltage 5.0 V_{EBO} Collector Current (DC) 1.0 Α IC(DC)





ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
ton	Turn-on Time		20	40	ns	Vcc = 10 V
^t off	Turn-off Time		72	110	ns	I _C = 500 mA
t _{stg}	Storage Time		55	80	ns	I _{B1} = −I _{B2} =50 mA
fT	Gain Bandwidth Product	300	380		MHz	$V_{CE} = 10 \text{ V, } I_{E} = -100 \text{ mA}$
Cob	Output Capacitance		1.8	10	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
hFE1**	DC Current Gain	60	120	200	_	V _{CE} = 10 V, I _C = 50 mA
hFE2**	DC Current Gain	60	150		_	$V_{CE} = 10 \text{ V, } I_{C} = 500 \text{ mA}$
VCE (sat) **	Collector Saturation Voltage		0.17	0.40	V	I _C = 500 mA, I _B = 50 mA
V _{BE(sat)**}	Base Saturation Voltage		0.90	1.20	V	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$
^I CES	Collector Cutoff Current			0.1	μΑ	V _{CE} = 45 V, R _{BE} = 0
IEBO	Emitter Cutoff Current			0.1	μΑ	V _{EB} = 4.0 V, I _C = 0

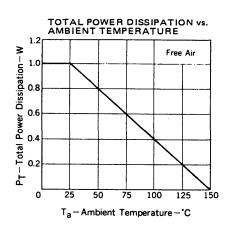
^{**} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

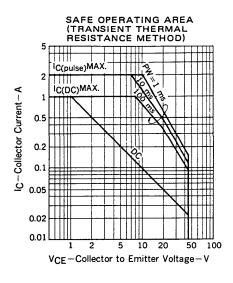
Classification of hee1

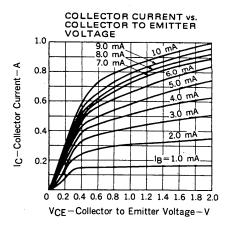
Rank	L	к				
Range	60 to 120	100 to 200				

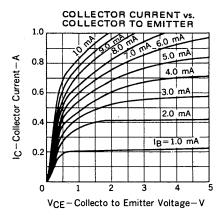
Test Conditions: VCE = 10 V, IC = 50 mA

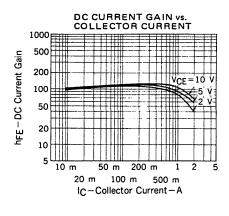
TYPICAL CHARACTERISTICS (Ta = 25 °C)

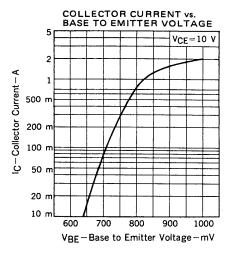


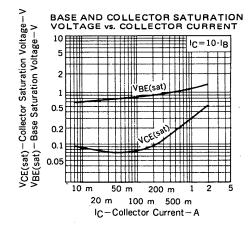


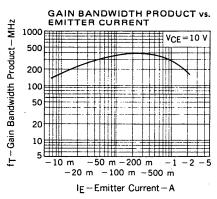


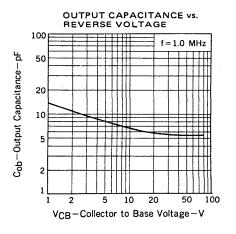


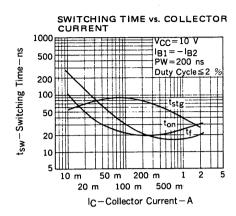












SWITCHING TIME TEST CIRCUIT

